



#### 80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX T <sub>C</sub> = +25°C
	25mΩ @ V <sub>GS</sub> = 10V	27A
80V	41mΩ @ V <sub>GS</sub> = 4.5V	21A

### **Description**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

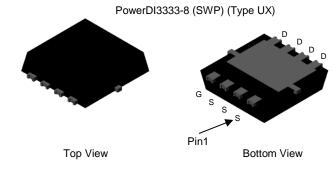
- Backlighting
- Power Management Functions
- DC-DC Converters

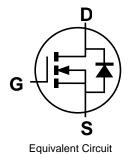
#### **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Small Form Factor, Thermally Efficient Package Enables Higher Density End Products
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.072 grams (Approximate)





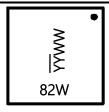
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH8028LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape and Reel
DMTH8028LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape and Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



82W = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 21 = 2021)

WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



## **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		VDSS	80	V
Gate-Source Voltage		$V_{GSS}$	±20	V
	Tc = +25°C		27	A
Continuous Drain Current (Note 7) V <sub>GS</sub> = 10V	T <sub>C</sub> = +100°C	lD	19	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	108	Α
Maximum Continuous Body Diode Forward Current (Note 7)		Is	27	Α
Pulsed Body Diode Forward Current	Ism	108	Α	
Avalanche Current, L = 0.3mH (Note 8)	las	12.5	Α	
Avalanche Energy, L = 0.3mH (Note 8)	Eas	23.4	mJ	

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 6)	PD	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	4.0	*C/VV
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C

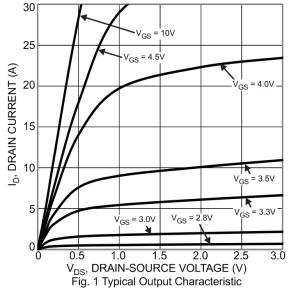
### Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

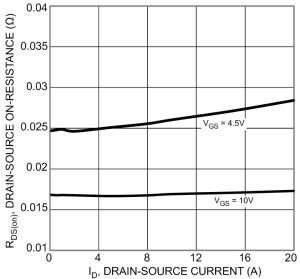
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(TH)	1.3	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Dagger	_	17	25	mΩ	$V_{GS} = 10V$ , $I_D = 5A$	
Static Brain Source on Resistance	R <sub>DS(ON)</sub>	_	26	41	11122	$V_{GS} = 4.5V, I_{D} = 4.5A$	
Diode Forward Voltage	VsD	_	0.8	1.2	V	$V_{GS} = 0V$ , $I_{S} = 5A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	631	_		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	200	_	pF		
Reverse Transfer Capacitance	Crss	_	19.5				
Gate Resistance	Rg	_	1.1		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.4	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	10.4	_	0	Vps = 40V. lp = 7.5A	
Gate-Source Charge	$Q_{gs}$	_	1.8	_	nC	VDS = 40V, ID = 7.5A	
Gate-Drain Charge	$Q_{gd}$	_	2.4				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.1	_			
Turn-On Rise Time	$t_R$	_	9.7	_	no	$V_{DD} = 40V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	18.6	_	ns	$R_G = 2.7\Omega$ , $I_D = 10A$	
Turn-Off Fall Time	tF	_	8.6	_			
Body Diode Reverse Recovery Time	trr	_	28.5	_	ns	I <sub>F</sub> = 7.5A, di/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Qrr	_	21.7	_	nC	$IF = I.3A$ , $uI/uI = IOOA/\mu S$	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.







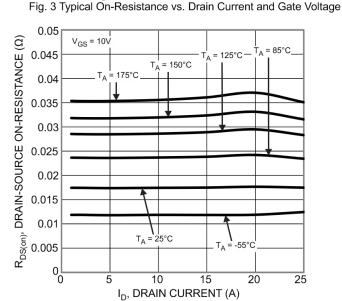
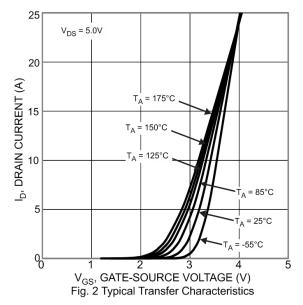
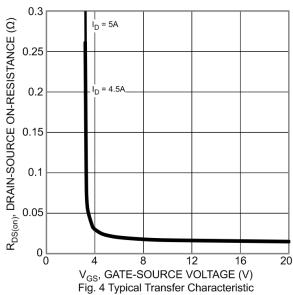


Fig. 5 Typical On-Resistance vs. Drain Current and Junction Temperature





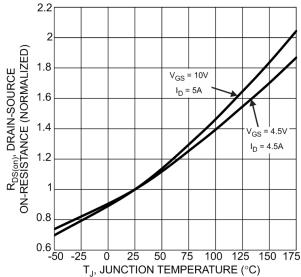


Fig. 6 On-Resistance Variation with Junction Temperature



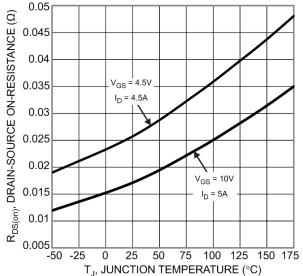
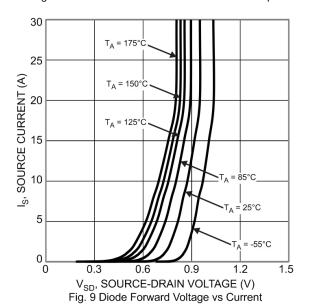


Fig. 7 On-Resistance Variation with Junction Temperature



10000 | Ciss | Coss | C

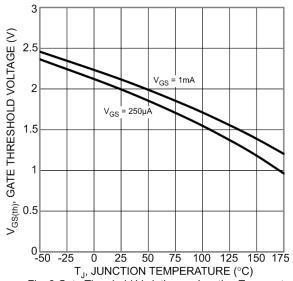


Fig. 8 Gate Threshold Variation vs Junction Temperature

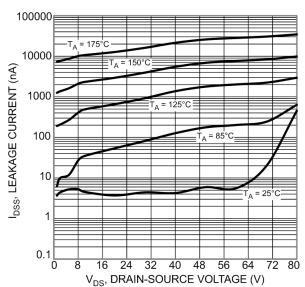
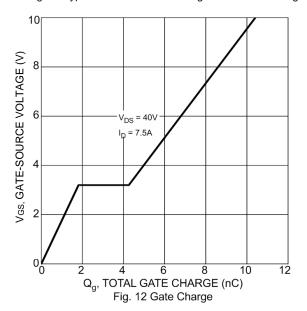
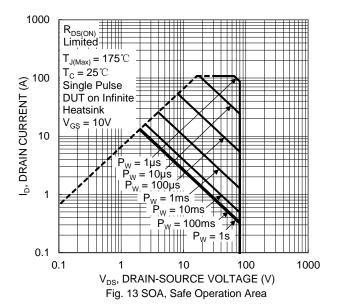
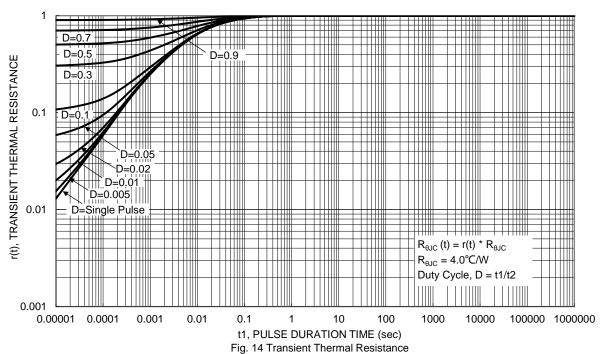


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage







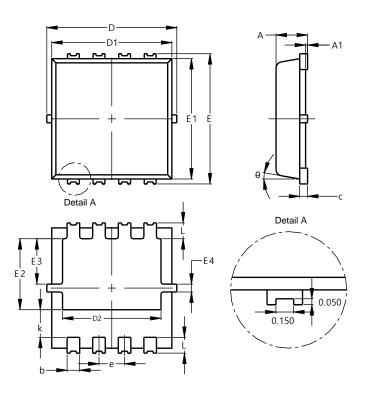




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)

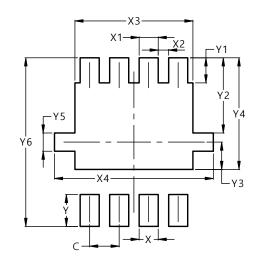


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min Max Ty		Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
E	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.600		
X4	3.500		
Y	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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